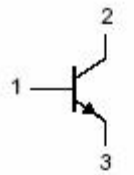
isc Silicon NPN Power Transistors — 2SD1237



PIN 1. BASE
2.COLLECTOR
3. EMITTER
TO-220C package

DESCRIPTION

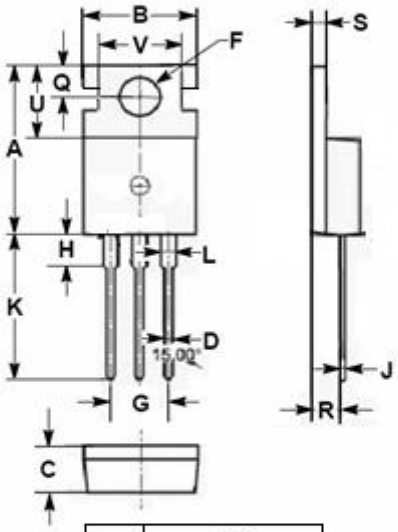
- Low Collector Saturation Voltage
  : $V_{CE(sat)}$= 0.4V(Max)@ I_C= 4A
- Large Current Capacity
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for relay drivers, high-speed inverters,converters, and other general high-current switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	7	A
I_{CP}	Collector Current-Pulse	12	A
P_C	Collector Power Dissipation @ T_a=25℃	1.75	W
	Collector Power Dissipation @ T_C=25℃	40	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

isc Silicon NPN Power Transistors 2SD1237

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 1mA; R_{BE}= ∞	120			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 4A; I_B= 0.4A			0.4	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 120V; I_E= 0			100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 4V; I_C= 0			100	μA
h_{FE-1}	DC Current Gain	I_C= 1A; V_{CE}= 2V	70		280	
h_{FE-2}	DC Current Gain	I_C= 4A; V_{CE}= 2V	30			
f_T	Current-Gain—Bandwidth Product	I_C= 1A; V_{CE}= 5V		20		MHz

Switching times

t_{on}	Turn-on Time	I_C= 2A; I_{B1}= I_{B2}= 0.2A R_L=1.67Ω; P_W=20μs; V_{CC}= 50V		0.1		μs
t_{stg}	Storage Time			1.6		μs
t_f	Fall Time			0.4		μs